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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	256КВ (256К х 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 1x12b, 3x16b; D/A 3x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f373cct7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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3.17 Timers and watchdogs

The STM32F373xx includes two 32-bit and nine 16-bit general-purpose timers, three basic timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary outputs
General- purpose	TIM2 TIM5	32-bit	Up, Down, Up/Down	Any integer between 1 and 65536	Yes	4	0
General- purpose	TIM3, TIM4, TIM19	16-bit	Up, Down, Up/Down	Any integer between 1 Yes and 65536		4	0
General- purpose	TIM12	16-bit	Up	Any integer between 1 No and 65536		2	0
General- purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General- purpose	TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	0
General- purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 Yes and 65536		1	1
Basic	TIM6, TIM7, TIM18	16-bit	Up	Any integer between 1 and 65536	Yes	0	0

 Table 5. Timer feature comparison



4 Pinouts and pin description



Figure 2. STM32F373xx LQFP48 pinout

1. The above figure shows the package top view.





Figure 4. STM32F373xx LQFP100 pinout



	Table 11. STM32F373xx pin definitions (continued)										
Pi	n nun	nber	S					Pin func	tions		
LQFP100	UFBGA100	LQFP64	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate function	Additional functions		
51	L12	-	-	VDDSD3	S	-	(2)	SDADC3 pov	ver supply		
52	K12	33	25	VREFSD+	S	-	-	External reference voltage for SDADC1, SDADC2, SI (positive input)			
53	K11	34	26	PB14	I/O	тс	(4)	SPI2_MISO/I2S2_MCK, USART3_RTS, TIM15_CH1, TIM12_CH1, TSC_G6_IO1	SDADC3_AIN8P		
54	K10	35	27	PB15	I/O	тс	(4)	SPI2_MOSI/I2S2_SD, TIM15_CH1N, TIM15_CH2, TIM12_CH2, TSC_G6_IO2, RTC_REFIN	SDADC3_AIN7P, SDADC3_AIN8M		
55	K9	36	28	PD8	I/O	тс	(4)	SPI2_SCK/I2S2_CK, USART3_TX, TSC_G6_IO3	SDADC3_AIN6P		
56	K8	-	-	PD9	I/O	тс	(4) (2)	USART3_RX, TSC_G6_IO4	SDADC3_AIN5P, SDADC3_AIN6M		
57	J12	-	-	PD10	I/O	тс	(4) (2)	USART3_CK	SDADC3_AIN4P		
58	J11	-	-	PD11	I/O	тс	(4) (2)	USART3_CTS	SDADC3_AIN3P, SDADC3_AIN4M		
59	J10	-	-	PD12	I/O	тс	(4) (2)	USART3_RTS, TIM4_CH1, TSC_G8_IO1	SDADC3_AIN2P		
60	H12	-	-	PD13	I/O	тс	(4) (2)	TIM4_CH2, TSC_G8_IO2	SDADC3_AIN1P, SDADC3_AIN2M		
61	H11	-	-	PD14	I/O	тс	(4) (2)	TIM4_CH3, TSC_G8_IO3	SDADC3_AIN0P		
62	H10	-	-	PD15	I/O	тс	(4) (2)	TIM4_CH4, TSC_G8_IO4	SDADC3_AIN0M		
63	E12	37	-	PC6	I/O	FT	(2)	TIM3_CH1, SPI1_NSS/I2S1_WS	-		



38

-

-

-

PC7

PC8

PC9

E11

E10 39

D12 40

64

65

66

TIM3_CH2,

SPI1_SCK/I2S1_CK,

SPI1_MISO/I2S1_MCK, TIM3_CH3

SPI1_MOSI/I2S1_SD, TIM3_CH4

(2)

(2)

(2)

FΤ

FΤ

FT

I/O

I/O

I/O

-

-

-

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	Table 13. Alternate functions for port PB												
Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF15
PB0	-	-	TIM3_CH3	TSC_ G3_IO3	-	SPI_MOSI/ I2S1_SD	-	-	-	-	TIM3_ CH2	-	EVENTOUT
PB1	-	-	TIM3_CH4	TSC_ G3_IO4	-	-	-	-	-	-	-	-	EVENTOUT
PB2	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
PB3	JTDO- TRACESWO	TIM2_ CH2	TIM4_ETR	TSC_ G5_IO1	-	SPI1_SCK/ I2S1_CK	SPI3_SCK/ I2S3_CK	USART2_TX	-	TIM13_ CH1	TIM3_ ETR	-	EVENTOUT
PB4	NJTRST	TIM16_ CH1	TIM3_CH1	TSC_ G5_IO2	-	SPI1_MISO /I2S1_MCK	SPI3_MISO/ I2S3_MCK	USART2_RX	-	TIM15_ CH1N	TIM17 _BKIN	-	EVENTOUT
PB5	-	TIM16_ BKIN	TIM3_CH2	-	I2C1_ SMBA	SPI1_MOSI /I2S1_SD	SPI3_MOSI /I2S3_SD	USART2_CK	-	-	TIM17 _CH1	TIM19 _ETR	EVENTOUT
PB6	-	TIM16_ CH1N	TIM4_CH1	TSC_ G5_IO3	I2C1_ SCL	-	-	USART1_TX	-	TIM15_ CH1	TIM3_ CH3	TIM19 _CH1	EVENTOUT
PB7	-	TIM17_ CH1N	TIM4_CH2	TSC_ G5_IO4	I2C1_ SDA	-	-	USART1_RX	-	TIM15_ CH2	TIM3_ CH4	TIM19 _CH2	EVENTOUT
PB8	-	TIM16_ CH1	TIM4_CH3	TSC_ SYNC	I2C1_ SCL	SPI2_SCK/ I2S2_CK	CEC	USART3_TX	COMP1 _OUT	CAN_ RX	-	TIM19 _CH3	EVENTOUT
PB9	-	TIM17_ CH1	TIM4_CH4	-	I2C1_ SDA	SPI2_NSS/ I2S2_WS	IR-OUT	USART3_RX	COMP2 _OUT	CAN_ TX	-	TIM19 _CH4	EVENTOUT
PB10	-	TIM2_ CH3	-	TSC_ SYNCH	-	SPI2_SCK/ I2S2_CK	CEC	USART3_TX	-	-	-	-	EVENTOUT
PB14	-	TIM15_ CH1	-	TSC_ G6_IO1	-	SPI2_MISO /I2S2_MCK	-	USART3_RTS	-	TIM12_ CH1	-	-	EVENTOUT
PB15	RTC_REFIN	TIM15_ CH2	TIM15_ CH1N	TSC_ G6_IO2	-	SPI2_MOSI /I2S2_SD	-	-	-	TIM12_ CH2	-	-	EVENTOUT

Pinouts and pin description

STM32F373xx

		Conditions			Typ@V _{DD} (V _{DD} =V _{DDA})						Max ⁽¹⁾		
Symbol	Parameter			2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	Т _А = 25 °С	Т _А = 85 °С	Т _А = 105 °С	Unit
Supply current in Stop mode I _{DDA} Supply current in Standby mode		Regulator in run mode, all oscillators OFF	1.99	2.07	2.19	2.33	2.46	2.64	10.8	11.8	12.4		
	DDSD12	Regulator in low-power mode, all oscillators OFF	1.99	2.07	2.18	2.32	2.47	2.63	10.6	11.5	12.5		
	and V _I	LSI ON and IWDG ON	2.44	2.53	2.7	2.89	3.09	3.33	-	-	-	μA	
	Standby mode	V _{DDA}	LSI OFF and IWDG OFF	1.87	1.94	2.06	2.19	2.35	2.51	4.1	4.5	4.8	
IDDAmon	Supply current for V _{DDA} and V _{DDSD12} monitoring		-	0.95	1.02	1.12	1.2	1.27	1.4	-	-	-	

|--|

1. Data based on characterization results and tested in production.

2. To obtain data with monitoring OFF is necessary to substract the IDDAmon current.

		-		Typ @ V _{BAT}							Max ⁽²⁾		
Symbol	Parameter	Conditions	= 1.65 V	= 1.8 V	= 2.0 V	= 2.4 V	= 2.7 V	= 3.3 V	= 3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit
I _{DD}	Backup domain	LSE & RTC ON; "Xtal mode" lower driving capability; LSEDRV[1:0] = '00'	0.50	0.52	0.55	0.63	0.70	0.87	0.95	1.1	1.6	2.2	
VBAT	supply current	LSE & RTC ON; "Xtal mode" higher driving capability; LSEDRV[1:0] = '11'	0.85	0.90	0.93	1.02	1.10	1.27	1.38	1.6	2.4	3.0	μΑ

Table 32. Typical and maximum current consumption from V_{BAT} supply⁽¹⁾

1. Crystal used: Abracon ABS07-120-32.768kHz-T with 6 pF of CL for typical values.

2. Guaranteed by characterization results.



				-	Гур		
Symbol	Parameter	Conditions	f _{HCLK}	Peripherals enabled	Peripherals disabled	Unit	
			72 MHz	61.4	28.8		
		Durania a farm 1105	64 MHz	55.4	25.9		
		crystal clock 8 MHz,	48 MHz	42.3	20.0		
		code executing	32 MHz	28.7	13.8		
	Supply current in Run mode from V _{DD} supply	IIOIII FIASII, FLL OII	24 MHz	21.9	10.7		
I			16 MHz	14.8	7.4		
DD			8 MHz	7.8	4.1	ma	
		Dunning from UCE	4 MHz	4.6	2.6		
		crystal clock 8 MHz,	2 MHz	2.9	1.8		
		code executing	1 MHz	2.0	1.3		
		ITOITI FIASTI, PLL OII	500 kHz	1.5	1.1		
			125 kHz	1.2	1.0		
			72 MHz	243.3	242.4	- μΑ	
	Supply current in	Dunning from UCE	64 MHz	214.3	213.3		
		crystal clock 8 MHz, code executing	48 MHz	159.3	158.3		
			32 MHz	107.7	107.3		
		ITOITI FIASH, FEE OIT	24 MHz	82.8	82.6		
ı (1)(2)			16 MHz	58.4	58.2		
'DDA` ´´ ´	V _{DDA} supply		8 MHz	1.2	1.2		
		Dunning from USE	4 MHz	1.2	1.2		
		crystal clock 8 MHz,	2 MHz	1.2	1.2		
		code executing	1 MHz	1.2	1.2	-	
		II UIII I IASII, F LL UII	500 kHz	1.2	1.2		
			125 kHz	1.2	1.2		
Isdadc12 + Isdadc3	Supply currents in Run mode from V_{DDSD12} and V_{DDSD3} (SDADCs are off)	-	-	2.5	1	μA	

Table 33. Typical current consumption in Run mode, code with data processing running from Flash

1. V_{DDA} monitoring is off, V_{DDSD12} monitoring is off.

2. When peripherals are enabled, power consumption of the analog part of peripherals such as ADC, DACs, Comparators, etc. is not included. Refer to those peripherals characteristics in the subsequent sections.



I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 52: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC and SDADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode. Under reset conditions all I/Os are configured in input floating mode - so if some inputs do not have a defined voltage level then they can generate additional consumption. This consumption is visible on V_{DD} supply and also on V_{DDSDx} supply because some I/Os are powered from SDADCx supply (all I/Os which have SDADC analog input functionality).

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 36: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: C = C_{INT} + C_{EXT} + C_S

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



On-chip peripheral current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- The given value is calculated by measuring the current consumption
 - with all peripherals clocked off;
 - with only one peripheral clocked on.
- Ambient operating temperature at 25°C and $V_{DD} = V_{DDA} = 3.3$ Volts.

Peripheral	Typical consumption ⁽¹⁾	Unit
AHB per	ripherals	-
BusMatrix ⁽²⁾	6.9	
DMA1	18.3	
DMA2	4.8	
CRC	2.6	
GPIOA	12.2	
GPIOB	11.9	
GPIOC	4.3	
GPIOD	12.0	
GPIOE	4.4	
GPIOF	3.7	μA/MHz
TSC	5.7	
APB2 pe	ripherals	
APB2-Bridge ⁽³⁾	4.2	
SYSCFG & COMP	2.8	
ADC1	17.7	
SPI1	12.3	
USART1	22.9	
TIM15	15.7	
TIM16	12.2	
TIM17	12.1	
TIM19	18.5	
SDAC1	10.8	
SDAC2	10.5	
SDAC3	10.3	

Table 36. Peripheral current consumption





Figure 13. Low-speed external clock source AC timing diagram

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 40*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Тур	Max ⁽²⁾	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
		During startup ⁽³⁾	-	-	8.5	
I _{DD}		V _{DD} = 3.3 V, Rm= 30 Ω CL= 10 pF@8 MHz	- 0.4 -			
		V _{DD} = 3.3 V, Rm= 45 Ω CL= 10 pF@8 MHz	-	0.5	-	
	HSE current consumption	V _{DD} = 3.3 V, Rm= 30 Ω CL=5 pF@32 MHz	-	0.8	-	mA
		V _{DD} = 3.3 V, Rm= 30 Ω CL= 10 pF@32 MHz	-	1	-	
		V _{DD} = 3.3 V, Rm= 30 Ω CL= 20 pF@32 MHz	- 1.5 -		-	
9 _m	Oscillator transconductance	Startup	10	-	-	mA/V
t _{SU(HSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	2	-	ms

Table 40. HSE c	oscillator	characteristics
-----------------	------------	-----------------

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by design.

3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time

 t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer



For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 14*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.





1. R_{EXT} value depends on the crystal characteristics.



6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_{A} = –40 to 105 $^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
t _{prog}	16-bit programming time	T _A = -40 to +105 °C	40	53.5	60	μs
t _{ERASE}	Page (2 kB) erase time	T _A = -40 to +105 °C	20	-	40	ms
t _{ME}	Mass erase time	T _A = -40 to +105 °C	20	-	40	ms
I _{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

Table 45. Flash memory	characteristics
------------------------	-----------------

1. Guaranteed by design.

Cumhal	Devenueter	Conditions	Value	l lasit
Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
N _{END}	Endurance	$T_A = -40$ to +85 °C (6 suffix versions) $T_A = -40$ to +105 °C (7 suffix versions)	10	kcycles
		1 kcycle ⁽²⁾ at T _A = 85 °C	30	
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 105 °C	10	Years
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	

Table 46. Flash memory endurance and data retention

1. Guaranteed by characterization results.

2. Cycling performed over the whole temperature range.



Symbol	bol Parameter Conditions		Min	Мах	Unit
DuCy(SCK) ⁽¹⁾	I2S slave input clock duty cycle	Slave mode	30	70	%
f _{CK} ⁽¹⁾	I ² S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.528	1.539	MHz
^{1/1} c(CK)		Slave mode	0	12.288	
$t_{r(CK)}^{(1)}$ $t_{f(CK)}$	I ² S clock rise and fall time	Capacitive load C _L = 30 pF	-	8	
t _{v(WS)} ⁽¹⁾	WS valid time	Master mode	4	-	
t _{h(WS)} ⁽¹⁾	WS hold time	Master mode	4	-	
t _{su(WS)} ⁽¹⁾	WS setup time	Slave mode	2	-	
t _{h(WS)} ⁽¹⁾	WS hold time	Slave mode	-	-	
t _{w(CKH)} ⁽¹⁾	I2S clock high time	Master f _{PCLK} = 16 MHz, audio frequency = 48 kHz	306	-	
t _{w(CKL)} ⁽¹⁾	I2S clock low time		312	-	
t _{su(SD_MR)} ⁽¹⁾	Data input actur time	Master receiver	6	-	
t _{su(SD_SR)} ⁽¹⁾	Data input setup time	Slave receiver	3	-	ns
t _{h(SD_MR)} ⁽¹⁾	Dete insut held time	Master receiver	1.5	-	
t _{h(SD_SR)} ⁽¹⁾		Slave receiver	1.5	-	
t _{v(SD_ST)} ⁽¹⁾	Data output valid time	Slave transmitter (after enable edge)	-	16	
t _{h(SD_ST)} ⁽¹⁾	Data output hold time	Slave transmitter (after enable edge)	16	-	
t _{v(SD_MT)} ⁽¹⁾	Data output valid time	Master transmitter (after enable edge)	-	2	
t _{h(SD_MT)} ⁽¹⁾	Data output hold time	Master transmitter (after enable edge)	0	-	

Table 59. I²S characteristics

1. Guaranteed by characterization results.



6.3.17 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 60* are preliminary values derived from tests performed under ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 22*.

Note: It is recommended to perform a calibration after each power-up.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DDA}	Power supply	-	2.4	-	3.6	V
V _{REF+}	Positive reference voltage	-	2.4	-	V _{DDA}	V
V _{REF-}	Negative reference voltage	-	0	-	-	V
I _{DDA(ADC)} ⁽¹⁾	Current consumption from $\mathrm{V}_{\mathrm{DDA}}$	$V_{DD} = V_{DDA} = 3.3 V$	-	0.9	-	mA
I _{VREF}	Current on the V _{REF} input pin	-	-	160 ⁽²⁾	220 ⁽²⁾	μA
f _{ADC}	ADC clock frequency	-	0.6	-	14	MHz
$f_S^{(3)}$	Sampling rate	-	0.05	-	1	MHz
f (3)	Extornal trigger frequency	f _{ADC} = 14 MHz	-	-	823	kHz
'TRIG` '		-	-	-	17	1/f _{ADC}
V _{AIN}	Conversion voltage range	-	0 (V _{SSA} or V _{REF-} tied to ground)	-	V _{REF+}	V
$R_{SRC}^{(3)}$	Signal source impedance	See Equation 1 and Table 61 for details	-	-	50	kΩ
R _{ADC} ⁽³⁾	Sampling switch resistance	-	-	-	1	kΩ
C _{ADC} ⁽³⁾	Internal sample and hold capacitor	-	-	-	8	pF
t (3)	Calibration time	f _{ADC} = 14 MHz	f _{ADC} = 14 MHz 5.9			μs
'CAL`		-	83			1/f _{ADC}
+. (3)	Injection trigger conversion	f _{ADC} = 14 MHz	-	-	0.214	μs
Hat	latency	-	-	-	2 ⁽⁴⁾	1/f _{ADC}
t. (3)	Regular trigger conversion	f _{ADC} = 14 MHz	-	-	0.143	μs
Hatr	latency	-	-	-	2 ⁽⁴⁾	1/f _{ADC}
$t_{a}(3)$	Sampling time	f _{ADC} = 14 MHz	0.107	-	17.1	μs
is		-	1.5	-	239.5	1/f _{ADC}
t _{STAB} ⁽³⁾	Power-up time	-	-	-	1	μs
	Total conversion time (including	f _{ADC} = 14 MHz	1	-	18	μs
t _{CONV} ⁽³⁾	sampling time)	-	14 to 252 (t _S for sampling +12.5 for successive approximation)			1/f _{ADC}

Tahlo	60		characteristics
Iable	ου.	ADC	CITALACIELISTICS

During conversion of the sampled value (12.5 x ADC clock period), an additional consumption of 100 μA on I_{DDA} and 60 μA on I_{DD} is present

2. Guaranteed by characterization results.

3. Guaranteed by design.

4. For external triggers, a delay of 1/f_{PCLK2} must be added to the latency specified in Table 60



- ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
 Any positive injection current within the limits specified for lawyour and Σlawyour in Section 6.3.14 does not
 - Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in Section 6.3.14 does not affect the ADC accuracy.
- 3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
- 4. Guaranteed by characterization results.



Figure 27. ADC accuracy characteristics





1. Refer to *Table 60* for the values of R_{SRC} , R_{ADC} and C_{ADC} .

 C_{parasitic} represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C_{parasitic} value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 9*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.



Symbol	Parameter			Con	ditions		Min	Тур	Max	Unit	Note								
				f _{ADC} = 1.5 MHz		V_{REFSD^+} = 3.3 ⁽³⁾	76	77	-										
		e	gain =1	f _{ADC} = 6		V _{REFSD+} = 1.2 ⁽⁴⁾	75	76	-										
		al mod	0,	MHz		V _{REFSD+} = 3.3	76	77	-										
		ifferenti		$f_{ADC} = 6$		V _{REFSD+} = 1.2 ⁽⁴⁾	70	74	-	dB									
	Signal to	Ω	gain =8	MHz		V _{REFSD+} = 3.3	79	85	-										
SINAD ⁽⁵⁾	noise and distortion		0,	f _{ADC} = 1.5 MHz	V _{DDSDx} = 3.3	V_{REFSD^+} = 3.3 ⁽³⁾	75	81	-		ENOB = SINAD/ 6.02 = 0.292								
	ratio			f _{ADC} = 1.5MHz		V _{REFSD+} = 3.3	72	73	-										
		mode	gain =1	f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	68	71	-										
			ended		6 MHz		V _{REFSD+} = 3.3	72	73	-									
		Single	8=	f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	60	64	-										
				gain	gain	gain	gain	gain	gain	gain	gain	gair	6 MHz	Hz	V _{REF} = 3.3	67	72	-	
					f _{ADC} = 1.5 MHz		V_{REFSD^+} = 3.3 ⁽³⁾	-	-77	-76									
		al mode	e L	le pain =1	le	e	le	le gain =1	e gain =1	e gain =1	le gain =1	gain = (f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	-	-77	-76	
									6 MHz		V _{REFSD+} = 3.3	-	-77	-76					
		ifferenti		f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	-	-85	-70										
тuр ⁽⁵⁾	Total harmonic distortion	Total	Ω	gain =8	6 MHz	V _{DDSDx}	V _{REFSD+} = 3.3	-	-93	-80	dD								
יישחו			0,	0,	0,	0,	0,	f _{ADC} = 1.5 MHz	= 3.3	V _{REFSD+} = 3.3 ⁽³⁾	-	-93	-83	uв	-				
			٩	ę	e	=	f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	-	-72	-68							
		ded mo	gain	6 MHz		V _{REFSD+} = 3.3	-	-74	-72										
		igle enc	8=	f _{ADC} =		V _{REFSD+} = 1.2 ⁽⁴⁾	-	-66	-61										
			Sin	gain	6 MHz		V _{REFSD+} = 3.3	-	-75	-70									

Table 74. SDADC characteristics (continued)⁽¹⁾



7.3 LQFP64 package information

Figure 38. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.







1. Dimensions are expressed in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking orientation versus pin 1 identifier location.



Figure 40. LQFP64 marking example (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



Date	Revision	Changes
18-Mar-2014	5	Renamed part number STM32F37x to STM32F373xx Added note1 in <i>Table 28: Typical and maximum current</i> <i>consumption from VDD supply at VDD</i> = $3.6 V$ Updated <i>Chapter 3.14: Digital-to-analog converter (DAC)</i> Updated, added note 2 and 3 in <i>Table 57: I2C analog filter</i> <i>characteristics</i> Renamed t _{SP} symbol with t _{AF.} Added note for EG Symbol in <i>Table 74: SDADC</i> <i>characteristics</i> Added all packages top view
21-Jul-2015	6	Updated Section 7 Updated Section 3.13 Updated Section 3.7.1, Section 3.7.4 Updated Table 11: STM32F373xx pin definitions, Table 19: Voltage characteristics, Table 49: ESD absolute maximum ratings, Table 74: SDADC characteristics, Table 76: UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data, and Table 78: LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data Updated Figure 2: STM32F373xx LQFP48 pinout, Figure 9: Power supply scheme, Figure 32: UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline, Figure 34: UFBGA100 marking example (package top view), Figure 36: LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint, Figure 37: LQFP100 marking example (package top view), Figure 38: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline, Figure 39: LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint, Figure 40: LQFP64 marking example (package top view), Figure 42: LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package recommended footprint, Figure 43: LQFP48 marking example (package top view). Added Table 32: Typical and maximum current consumption from VBAT supply, Table 49: ESD absolute maximum ratings, Table 64: Comparator characteristics, Table 77: UFBGA100 recommended PCB design rules (0.5 mm pitch BGA). Added Figure 11: Typical VBAT current consumption (LSE and RTC ON/LSEDRV[1:0]='00'), Figure 30: Maximum VREFINT scaler startup time from power down, Figure 33: UFBGA100 - 100-pin, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package recommended footprint.

Table 83. Document revision history (continued)

